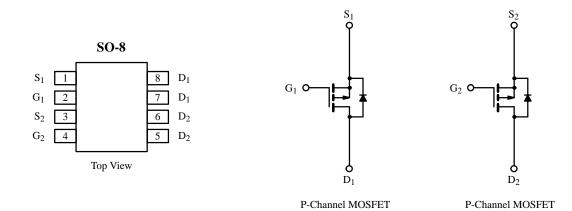
### **Dual P-Channel 30-V (D-S) Rated MOSFET**

### **Product Summary**

V <sub>DS</sub> (V)	$\mathbf{r_{DS(on)}}(\Omega)$	$I_{D}(A)$	
-30	$0.085 @ V_{GS} = -10 V$	±3.5	
-30	0.19 @ V <sub>GS</sub> = -4.5 V	±2.5	



### Absolute Maximum Ratings ( $T_A = 25^{\circ}C$ Unless Otherwise Noted)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		$V_{\mathrm{DS}}$	-30	V	
Gate-Source Voltage		$V_{GS}$	±20		
Continuous Drain Current (T <sub>I</sub> = 150°C) <sup>a</sup>	$T_A = 25^{\circ}C$	I <sub>D</sub>	± 3.5	A	
Continuous Drain Current (1j = 130 C)	$T_A = 70^{\circ}C$		± 2.8		
Pulsed Drain Current		$I_{DM}$	±20	A	
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	-1.7		
Maximum Power Dissipation <sup>a</sup>	$T_A = 25^{\circ}C$	P <sub>D</sub>	2.0	w	
Maximum Fower Dissipation	$T_A = 70^{\circ}C$	1 D	1.3	**	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 150	°C	

### **Thermal Resistance Ratings**

Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	62.5	°C/W

### Notes

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70156. A SPICE Model data sheet is available for this product (FaxBack document #70554).

a. Surface Mounted on FR4 Board,  $t \le 10$  sec.

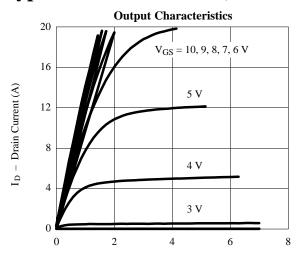
# **Si4947DY**

# Specifications ( $T_J = 25^{\circ}C$ Unless Otherwise Noted)

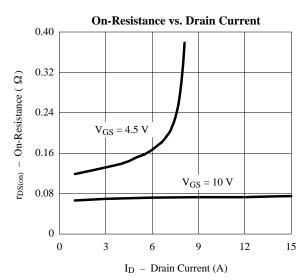
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Static						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \mu A$	1.0			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zone Cote Walters Durin Comment		$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-25	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} \ge -5 \text{ V}, V_{GS} = -10 \text{ V}$	-15			А
Dig Ogu Diu		$V_{GS} = -10 \text{ V}, I_D = 2.5 \text{ A}$		0.066	0.085	Ω
Drain-Source On-State Resistance <sup>b</sup>	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = 1.8 \text{ A}$		0.125	0.19	
Forward Transconductance <sup>b</sup>	gfs	$V_{DS} = -15 \text{ V}, I_D = -2.5 \text{ A}$		5.0		S
Diode Forward Voltage <sup>b</sup>	$V_{\mathrm{SD}}$	$I_S = -1.7 \text{ A}, V_{GS} = 0 \text{ V}$		-0.8	-1.2	V
Dynamic <sup>a</sup>						•
Total Gate Charge	Qg			8.7	15	nC
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -10 \text{ V}, \ V_{GS} = -10 \text{ V}, I_D = -2.5 \text{ A}$		1.9		
Gate-Drain Charge	$Q_{\mathrm{gd}}$			1.3		
Turn-On Delay Time	t <sub>d(on)</sub>			7	15	
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V, } R_L = 10 \Omega$ $I_D \cong -1 \text{ A, } V_{GEN} = -10 \text{ V, } R_G = 6 \Omega$		9	18	ns
Turn-Off Delay Time	$t_{d(off)}$			14	27	
Fall Time	$t_{\mathrm{f}}$			8	15	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	$I_F = -1.7 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		50	80	1

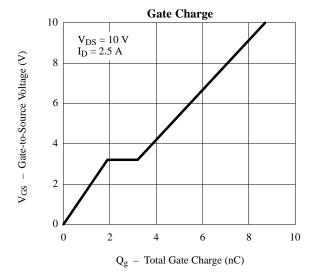
<sup>a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.</sup> 

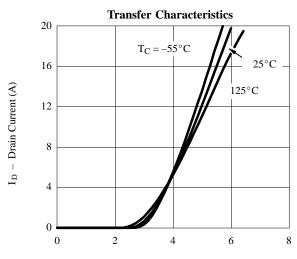
### **Typical Characteristics (25°C Unless Otherwise Noted)**



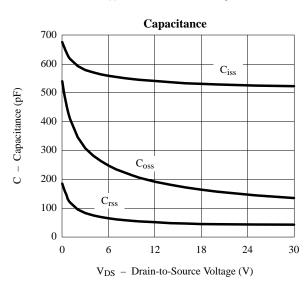
 $V_{DS}$  – Drain-to-Source Voltage (V)

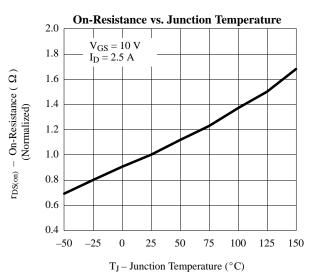




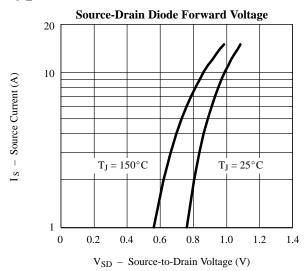


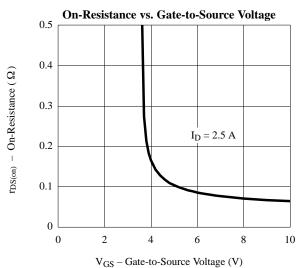
V<sub>GS</sub> - Gate-to-Source Voltage (V)

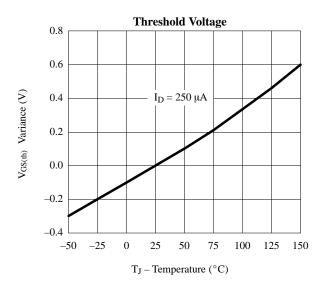


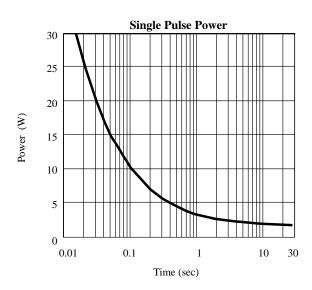


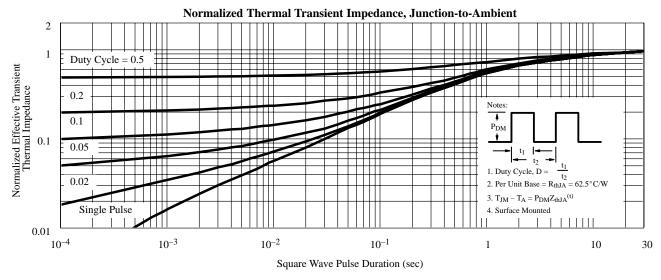
### Typical Characteristics (25°C Unless Otherwise Noted)











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